

SPACE COMPONENTS NEWSLETTER November 2022

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RadHard GaN HEMT



40V 4mΩ 530A

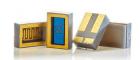
100V 6mΩ 90A

200V 28mΩ 20A

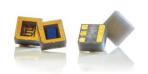


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Easy-to-Use Demonstration Boards







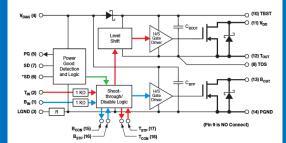
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FBS-GAM02-P-R50

50 VDC / 10 A Radiation-Hardened Multifunction Power Module

Four Possible Configurations:

- Single Low-Side Gate Driver
- Single High-Side Gate Driver
- Independent Low- and High-Side Drivers
- Half-Bridge Gate Drivers with Input Shoot-through Protection



Protec GmbH High-Rel Electronic Components

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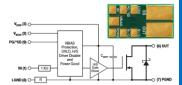
c.mayer@protec-semi.com



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FBS-GAM01-P-R100

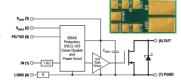
100 VDC / 12 A Radiation-Hardened Single Low-Side Power Diver Module



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FBS-GAM01-P-R50

50 VDC / 12 A Radiation-Hardened Single Low-Side Power Diver Module



RENESAS intersil

ISL70040SEH and ISL73040SEH

Low-side drivers to drive enhancement mode GaN FETs in isolated topologies and boost type configurations. Supply voltage from 4. 5V to 13.

Gate drive voltage of 4. 5V (V_{DRV}) generated using an internal regulator which prevents the gate voltage from exceeding the maximum gate-source rating of enhancement mode GaN FETs.

The ISL70040SEH and ISL73040SEH inputs can withstand voltages up to 14. 7V regardless of the $V_{\rm DD}$ voltage. This allows the ISL70040SEH and ISL73040SEH inputs to be connected directly to most PWM controllers.

